

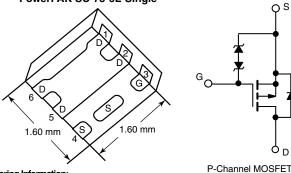
Vishay Siliconix

P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	R _{DS(on)} (Ω) Max.	I _D (A)	Q _g (Typ.)						
	0.0255 at V _{GS} = - 4.5 V	- 9 ^a							
	0.0280 at V _{GS} = - 3.7 V	- 9 ^a							
- 12	0.0360 at V _{GS} = - 2.5 V	- 9 ^a	13.4 nC						
	0.0600 at V _{GS} = - 1.8 V	- 9 ^a							
	0.1150 at V _{GS} = - 1.5 V	- 2							

PowerPAK SC-75-6L-Single

SiB441EDK-T1-GE3 (Lead (Pb)-free and Halogen-free)



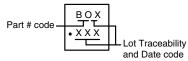
FEATURES

- TrenchFET[®] Power MOSFET
- Thermally Enhanced PowerPAK[®] SC-75 Package
 - Small Footprint Area
 - Low On-Resistance
- Typical ESD Performance 2500 V
- 100 % R_g Tested
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Portable Devices such as Smart Phones, Tablet PCs and Mobile Computing
 - Battery Switch
 - Load Switch
 - Power Management

Marking Code



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted) Parameter Symbol Limit Unit - 12 Drain-Source Voltage V_{DS} v Gate-Source Voltage V_{GS} ± 8 T_C = 25 °C - 9^a T_C = 70 °C - 9^a Continuous Drain Current (T_J = 150 °C) I_D T_A = 25 °C - 8.3^{b, c} T_A = 70 °C - 6.6^{b, c} Α - 40 Pulsed Drain Current (t = $300 \ \mu s$) I_{DM} - 9^a T_C = 25 °C Continuous Source-Drain Diode Current IS T_A = 25 °C - 2^{b, c} T_C = 25 °C 13 T_C = 70 °C 84 Maximum Power Dissipation P_D W $T_A = 25 \degree C$ 2.4^{b, c} $\overline{T_A = 70 \ ^{\circ}C}$ 1.6^{b, c} Operating Junction and Storage Temperature Range - 55 to 150 T_J, T_{sta} °C Soldering Recommendations (Peak Temperature)^{d, e} 260

THEDMAL DECISTANCE DATINGS

Parameter	Symbol	Typical	Maximum	Unit					
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	41	51	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	7.5	9.5	0/ 11				

Notes:

a. Package limited.

Ordering Information:

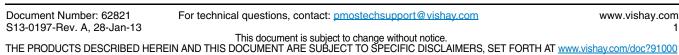
b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s

d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 105 °C/W.



HALOGEN FREE

Vishay Siliconix



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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit				
Static	-					1				
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 12			V				
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$			- 5		mV/°C				
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = - 250 μΑ		2.7						
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 0.4		- 0.9	V				
		$V_{DS} = 0 V, V_{GS} = \pm 8 V$			± 4	μΑ				
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 4.5 V$			± 1					
7		V _{DS} = - 12 V, V _{GS} = 0 V			- 1					
Zero Gate Voltage Drain Current	IDSS	V_{DS} = - 12 V, V_{GS} = 0 V, T_{J} = 55 °C			- 10					
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le$ - 5 V, V_{GS} = - 4.5 V	- 15			Α				
		V _{GS} = - 4.5 V, I _D = - 4 A		0.0210	0.0255					
		V _{GS} = - 3.7 V, I _D = - 4 A		0.0230	0.0280	Ω				
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 2 A		0.0290	0.0360					
	. ,	V _{GS} = - 1.8 V, I _D = - 2 A		0.0420	0.0600					
		V _{GS} = - 1.5 V, I _D = - 0.5 A		0.0570	0.1150	0				
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 6 V, I _D = - 4 A		17		S				
Dynamic ^b				•						
Input Capacitance	C _{iss}			1180		pF				
Output Capacitance	C _{oss}	V _{DS} = - 6 V, V _{GS} = 0 V, f = 1 MHz		265						
Reverse Transfer Capacitance	C _{rss}			250						
	Qg	V _{DS} = - 6 V, V _{GS} = - 8 V, I _D = - 2.1 A		22.1	33	nC				
Total Gate Charge				13.4	20					
Gate-Source Charge	Q _{gs}	$V_{DS} = -6 V$, $V_{GS} = -4.5 V$, $I_{D} = -2.1 A$		1.6						
Gate-Drain Charge	Q _{gd}			3.4						
Gate Resistance	R _g	f = 1 MHz	2.2	11	22	Ω				
Turn-On Delay Time	t _{d(on)}			22	45					
Rise Time	tr	V_{DD} = - 6 V, R_L = 2.7 Ω		42	85					
Turn-Off Delay Time	t _{d(off)}	$\rm I_D \cong$ - 2.2 A, $\rm V_{GEN}$ = - 4.5 V, $\rm R_g$ = 1 Ω		60	120	1				
Fall Time	t _f			50	100					
Turn-On Delay Time	t _{d(on)}			7	15	ns				
Rise Time	t _r	V_{DD} = - 6 V, R_L = 2.7 Ω		10	20					
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 2.2 A, V_{GEN} = - 8 V, R_g = 1 Ω		60	120					
Fall Time	t _f			52	100	1				
Drain-Source Body Diode Characteristi	cs				•					
Continuous Source-Drain Diode Current	۱ _S	T _C = 25 °C			- 9	A				
Pulse Diode Forward Current	I _{SM}				- 40					
Body Diode Voltage	V _{SD}	I _S = - 2.2 A, V _{GS} = 0 V		- 0.85	- 1.2	V				
Body Diode Reverse Recovery Time	t _{rr}			30	60	ns				
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = - 2.2 A, dl/dt = 100 A/μs, T _J = 25 °C		12	25	nC				
Reverse Recovery Fall Time	t _a	$F = -2.2 \text{ A}, \text{ u/ul} = 100 \text{ A/} \mu \text{s}, 1 \text{ J} = 25 \text{ °C}$		9						
Reverse Recovery Rise Time	t _b			11		ns				

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Document Number: 62821 For technical questions, contact: pmostechsupport@vishay.com www.vishay.com S13-0197-Rev. A, 28-Jan-13

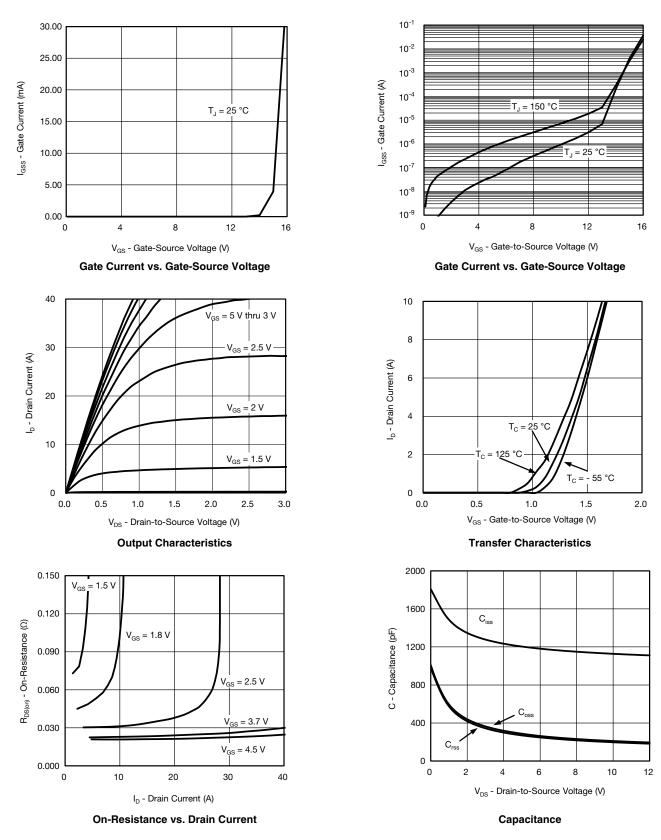
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



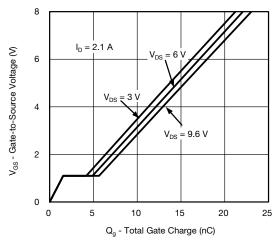
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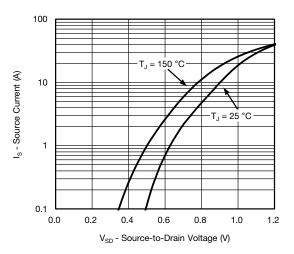
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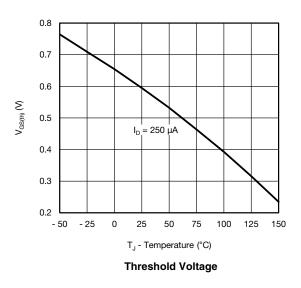
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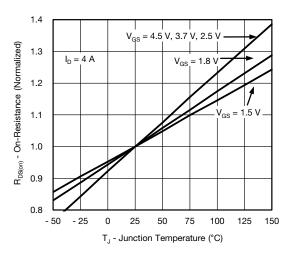




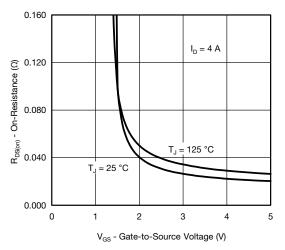


Soure-Drain Diode Forward Voltage

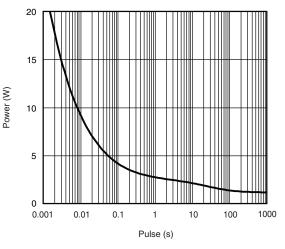




On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient

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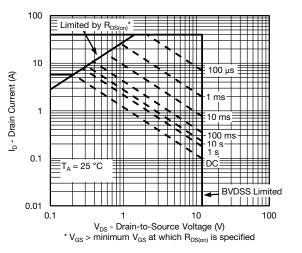
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New Product

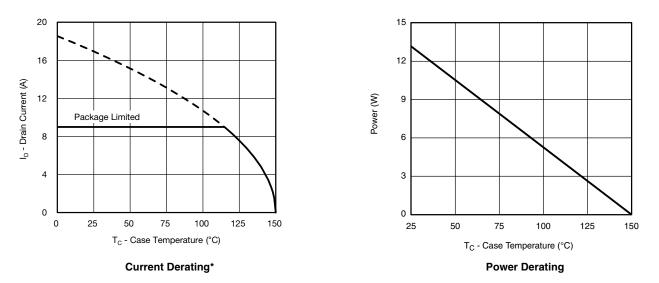


SiB441EDK Vishay Siliconix

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Safe Operating Area, Junction-to-Ambient

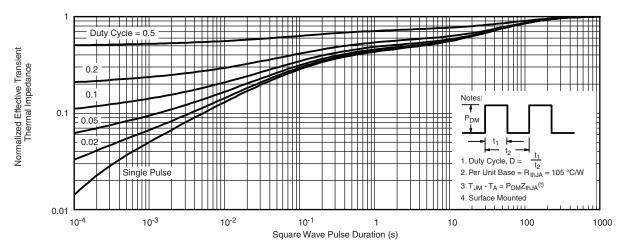


* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

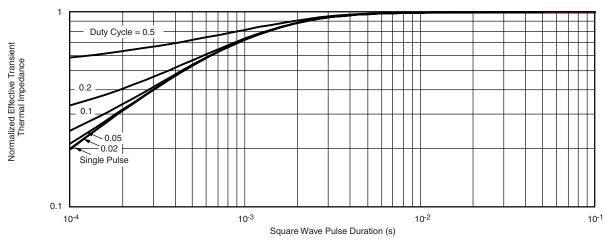


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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



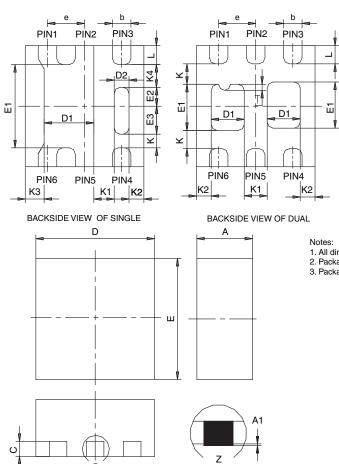
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62821.

Package Information

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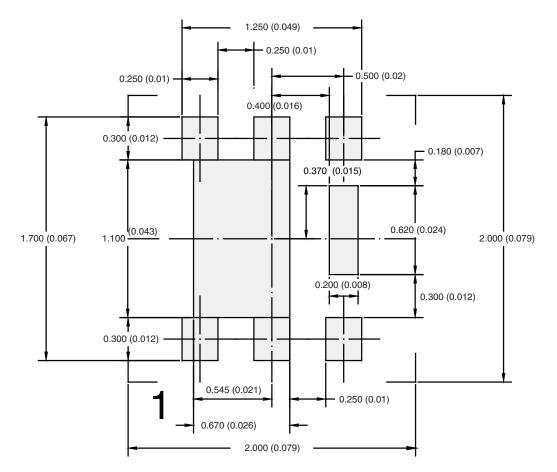
- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

DETAIL Z

	SINGLE PAD					DUAL PAD							
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES			
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067	
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021	
D2	0.10	0.20	0.30	0.004	0.008	0.012							
Е	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067	
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028	
E2	0.20	0.25	0.30	0.008	0.010	0.012							
E3	0.32	0.37	0.42	0.013	0.015	0.017							
е	0.50 BSC			0.020 BSC			0.50 BSC			0.020 BSC			
К	0.180 TYP 0.007 TYP				0.245 TYP			0.010 TYP					
K1	0.275 TYP 0.011 TYP			0.320 TYP			0.013 TYP						
K2		0.200 TYP 0.008 TYP				0.200 BSC		0.008 TYP					
K3		0.255 TYP 0.010 TYP											
K4	0.300 TYP			0.012 TYP									
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014	
Т							0.03	0.08	0.13	0.001	0.003	0.005	
ECN: C-07431 – Rev. C, 06-Aug-07 DWG: 5935													



RECOMMENDED PAD LAYOUT FOR PowerPAK[®] SC75-6L Single



Dimensions in mm/(Inches)

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